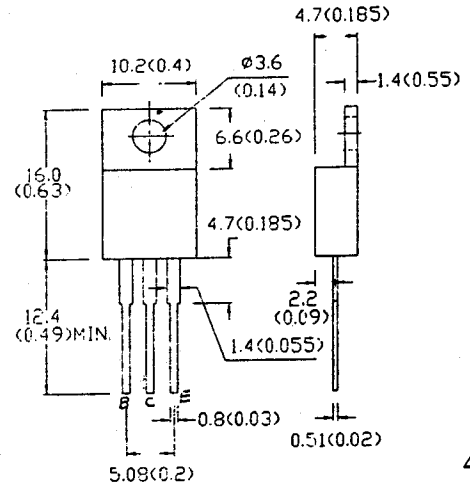


## DESCRIPTION

BD437 is silicon epitaxial-base NPN power transistor, intended for use in medium power linear and switching applications.



## ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	45V
Collector-Emitter Voltage	VCES	45V
Collector-Base Voltage	VCEO	45V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	4A
Collector Peak Current (t<10ms)	ICM	7A
Continuous Power Dissipation	Pd	36W
Operating & Storage Junction Temperature	Tj, Tstg	-65 to +150°C

## ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Collector Cutoff Current	ICBO			100	μA	VCB=45V IE=0
Collector Cutoff Current	ICES			100	μA	VCE=45V VBE=0
Emitter Cutoff Current	IEBO			1	mA	VEB=5V IC=0
Collector-Emitter Breakdown Voltage	LVCEO*	45			V	IC=10mA IB=0
Collector-Emitter Saturation Voltage	VCE(sat)*			0.6	V	IC=2A IB=0.2A
Base-Emitter Voltage	VBE*			1.2	V	IC=2A VCE=1V
D.C. Current Gain	HFE*	30	130			IC=10mA VCE=5V
		85	140			IC=500mA VCE=1V
		40				IC=2A VCE=1V
Current Gain Bandwidth Product	fT*	3			MHz	IC=250mA VCE=1V

\* Pulse Test : Pulse Width <300μs, Duty Cycle <2%.



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